

# PolarHT™ Power MOSFET

**IXTK 100N25P**  
**IXTQ 100N25P**  
**IXTT 100N25P**

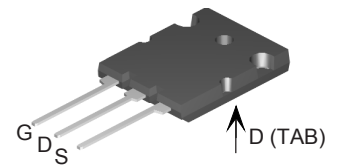
**V<sub>DSS</sub> = 250 V**  
**I<sub>D25</sub> = 100 A**  
**R<sub>DS(on)</sub> ≤ 27 mΩ**

N-Channel Enhancement Mode  
Avalanche Rated

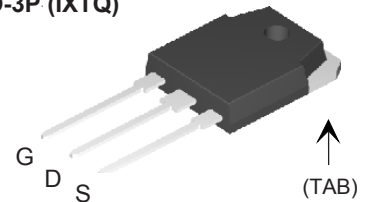


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25° C to 150° C	250	V
V <sub>DGR</sub>	T <sub>J</sub> = 25° C to 150° C; R <sub>GS</sub> = 1 MΩ	250	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25° C	100	A
I <sub>D(RMS)</sub>	External lead current limit	75	A
I <sub>DM</sub>	T <sub>C</sub> = 25° C, pulse width limited by T <sub>JM</sub>	250	A
I <sub>AR</sub>	T <sub>C</sub> = 25° C	60	A
E <sub>AR</sub>	T <sub>C</sub> = 25° C	60	mJ
E <sub>AS</sub>	T <sub>C</sub> = 25° C	2.0	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150° C, R <sub>G</sub> = 4 Ω	10	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25° C	600	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.062 in.) from case for 10 s	300	°C
T <sub>SOLD</sub>	Plastic body for 10 s	260	°C
M <sub>d</sub>	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-3P	5.5	g
	TO-264	10	g
	TO-268	5.0	g

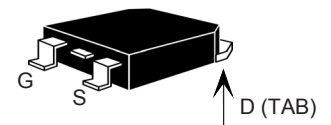
TO-264 (IXTK)



TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate      D = Drain  
S = Source    TAB = Drain

## Features

- † International standard packages
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance  
- easy to drive and to protect

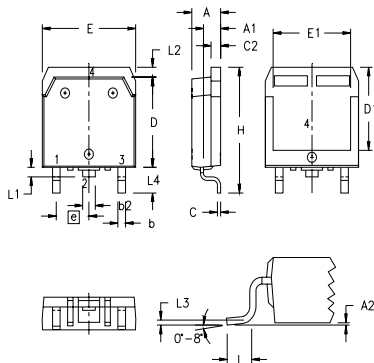
## Advantages

- † Easy to mount
- † Space savings
- † High power density

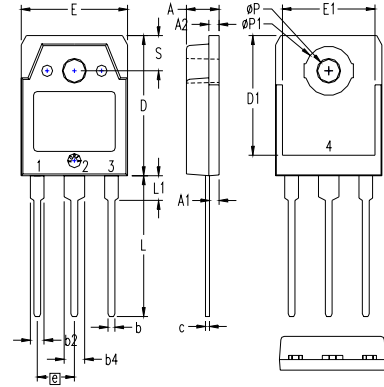
Symbol	Test Conditions (T <sub>J</sub> = 25° C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	250		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5		5.0 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> V <sub>GS</sub> = 0 V      T <sub>J</sub> = 125° C			25 μA
				250 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			27 mΩ

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = 0.5 I_{D25}$ , pulse test	40	56	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		6300	pF
$C_{oss}$			1150	pF
$C_{rss}$			240	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = I_{D25}$ $R_G = 3.3\ \Omega$ (External)		25	ns
$t_r$			26	ns
$t_{d(off)}$			100	ns
$t_f$			28	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$		185	nC
$Q_{gs}$			43	nC
$Q_{gd}$			91	nC
$R_{thJC}$				$0.21^\circ\text{C/W}$
$R_{thCS}$	TO-3P		0.21	$^\circ\text{C/W}$
$R_{thCS}$	TO-264		0.15	$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			100 A
$I_{SM}$	Repetitive			250 A
$V_{SD}$	$I_F = I_s$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ , $V_{GS} = 0\text{ V}$		200	ns
$Q_{RM}$			3.0	$\mu\text{C}$

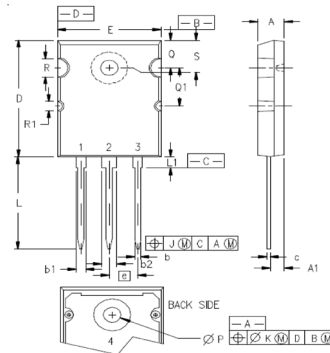
**TO-268 (IXTT) Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

**TO-3P (IXTQ) Outline**


- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
$\phi P$	.126	.134	3.20	3.40
$\phi P1$	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

**TO-264 (IXTK) Outline**


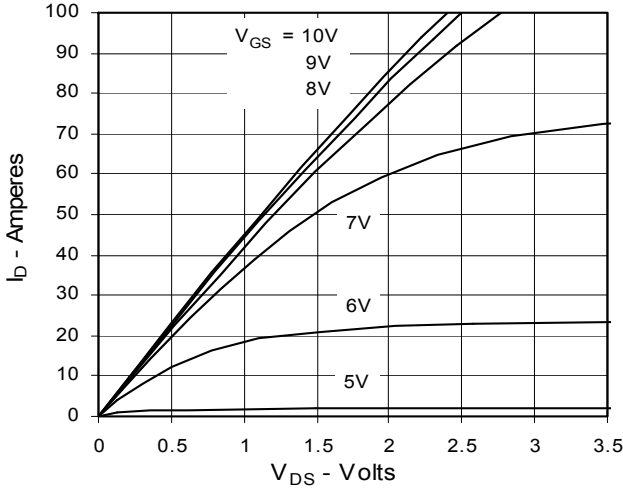
- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
$\phi P$	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
$\phi R$	.155	.187	3.94	4.75
$\phi R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

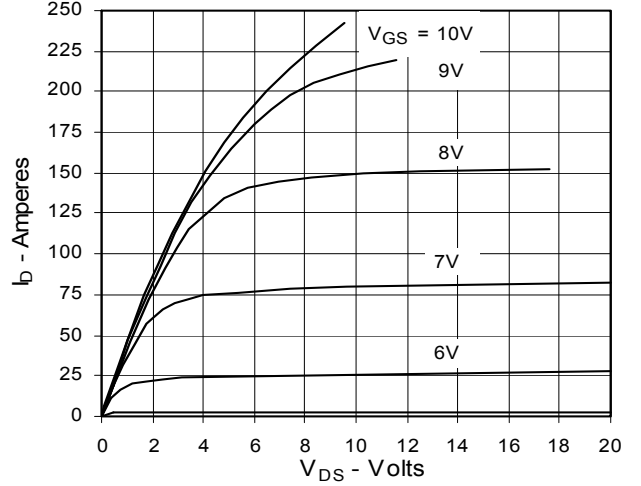
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585  
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4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

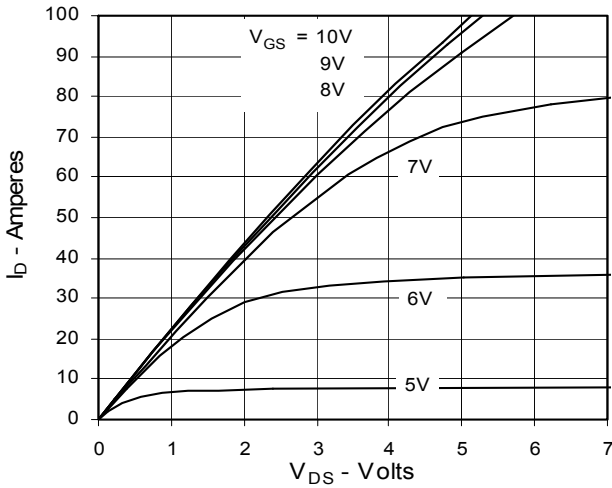
**Fig. 1. Output Characteristics  
@ 25°C**



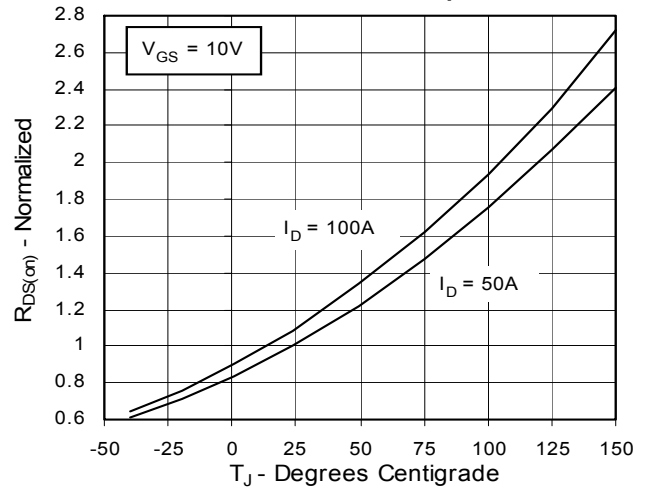
**Fig. 2. Extended Output Characteristics  
@ 25°C**



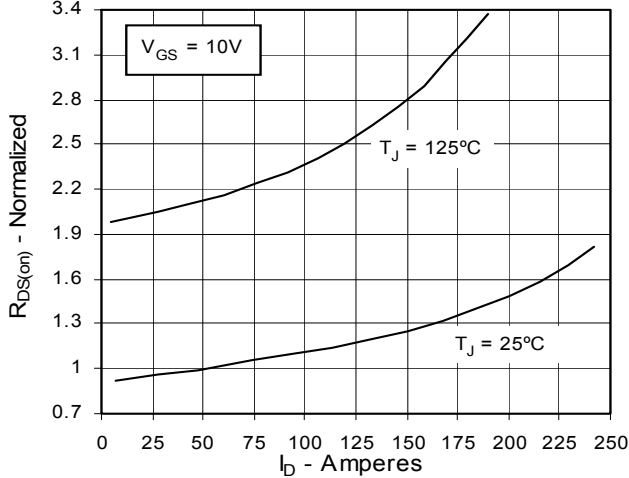
**Fig. 3. Output Characteristics  
@ 125°C**



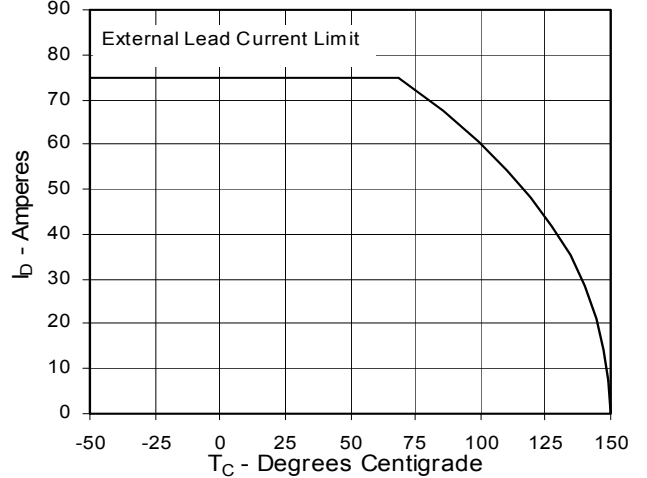
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$   
Value vs. Junction Temperature**



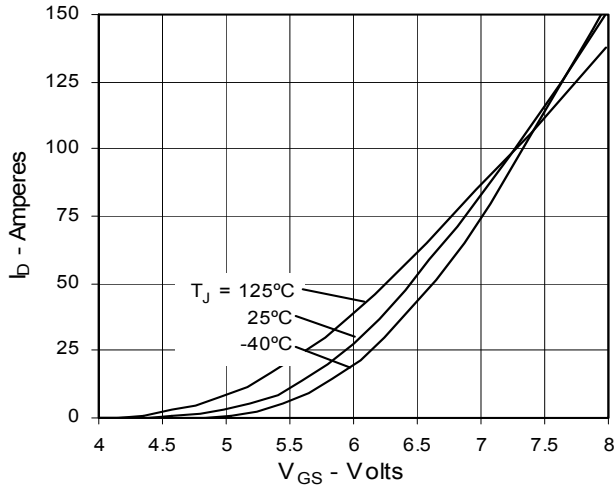
**Fig. 5.  $R_{DS(on)}$  Normalized to  
0.5  $I_{D25}$  Value vs.  $I_D$**



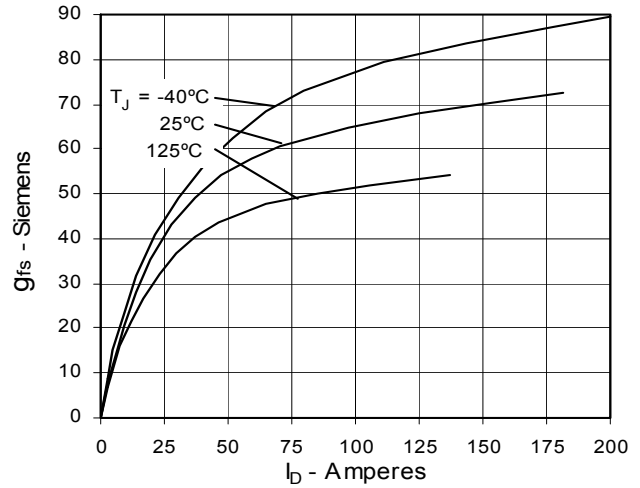
**Fig. 6. Drain Current vs. Case  
Temperature**



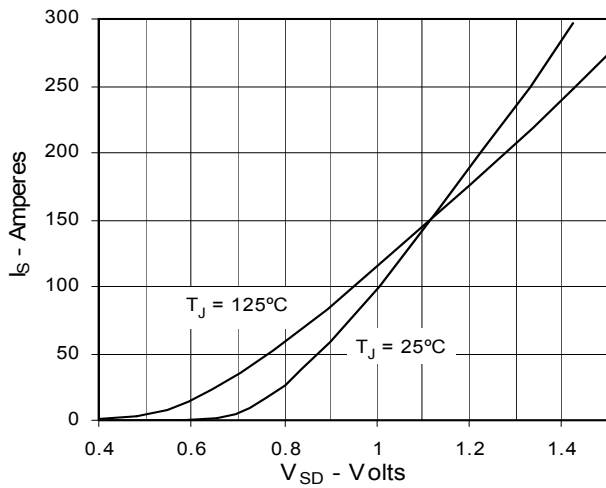
**Fig. 7. Input Admittance**



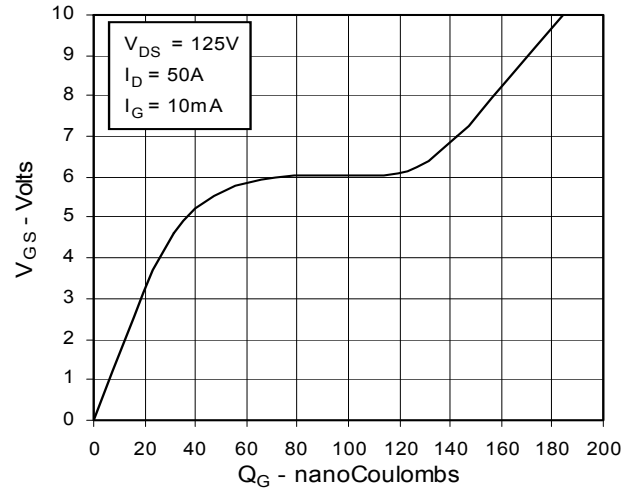
**Fig. 8. Transconductance**



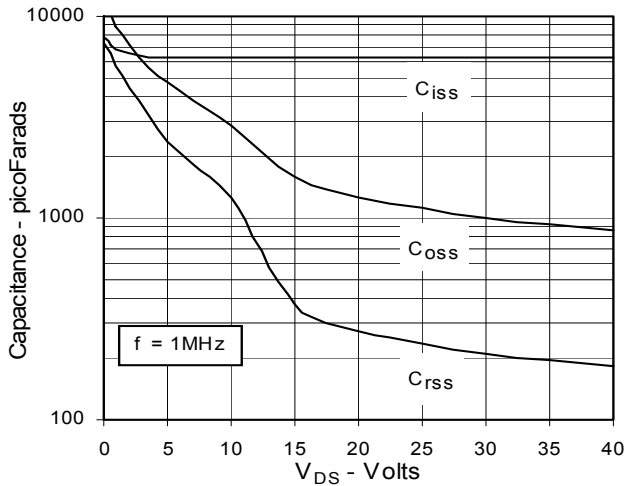
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

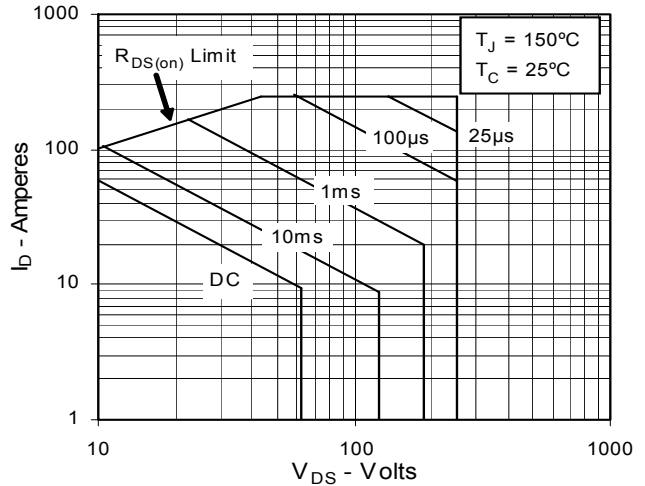


Fig. 13. Maximum Transient Thermal Resistance

